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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	Not Yet Assigned
				Filing Date	October 29, 2003
				First Named Inventor	Li Li
				Art Unit	<del>Not Yet Assigned</del> 2823
				Examiner Name	<del>Not Yet Assigned</del> J. PHAM
Sheet	1	of	11	Attorney Docket Number	M4065.0909/P909-A

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Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)					
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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>		Application Number	Not Yet Assigned
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		First Named Inventor	Li Li
		Group Art Unit	Not Yet Assigned 2823
		Examiner Name	Not Yet Assigned T. P. HAM
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		Examiner Name	Not Yet Assigned T. PHAM		
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